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### Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

#### Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	128
Total RAM Bits	-
Number of I/O	56
Number of Gates	3000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	100-LQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microsemi/ex64-tqg100i">https://www.e-xfl.com/product-detail/microsemi/ex64-tqg100i</a>

## Temperature Grade Offerings

Device\ Package	TQ64	TQ100
eX64	C, I, A	C, I, A
eX128	C, I, A	C, I, A
eX256	C, I, A	C, I, A

*Note:* C = Commercial

I = Industrial

A = Automotive

## Speed Grade and Temperature Grade Matrix

	–F	Std	–P
C	✓	✓	✓
I		✓	✓
A		✓	

*Note:* P = Approximately 30% faster than Standard

–F = Approximately 40% slower than Standard

Refer to the [eX Automotive Family FPGAs](#) datasheet for details on automotive temperature offerings.

Contact your local Microsemi representative for device availability.

Table 1-2 describes the I/O features of eX devices. For more information on I/Os, refer to [Microsemi eX, SX-A, and RT54SX-S I/Os](#) application note.

**Table 1-2 • I/O Features**

Function	Description
Input Buffer Threshold Selection	<ul style="list-style-type: none"> <li>• 5.0V TTL</li> <li>• 3.3V LVTTTL</li> <li>• 2.5V LVCMOS2</li> </ul>
Nominal Output Drive	<ul style="list-style-type: none"> <li>• 5.0V TTL/CMOS</li> <li>• 3.3V LVTTTL</li> <li>• 2.5V LVCMOS 2</li> </ul>
Output Buffer	<p>“Hot-Swap” Capability</p> <ul style="list-style-type: none"> <li>• I/O on an unpowered device does not sink current</li> <li>• Can be used for “cold sparing”</li> </ul> <p>Selectable on an individual I/O basis</p> <p>Individually selectable low-slew option</p>
Power-Up	<p>Individually selectable pull ups and pull downs during power-up (default is to power up in tristate)</p> <p>Enables deterministic power-up of device</p> <p><math>V_{CCA}</math> and <math>V_{CCI}</math> can be powered in any order</p>

The eX family supports mixed-voltage operation and is designed to tolerate 5.0 V inputs in each case.

A detailed description of the I/O pins in eX devices can be found in ["Pin Description"](#) on page 1-31.

## Hot-Swapping

eX I/Os are configured to be hot-swappable. During power-up/down (or partial up/down), all I/Os are tristated, provided  $V_{CCA}$  ramps up within a diode drop of  $V_{CCI}$ .  $V_{CCA}$  and  $V_{CCI}$  do not have to be stable during power-up/down, and they do not require a specific power-up or power-down sequence in order to avoid damage to the eX devices. In addition, all outputs can be programmed to have a weak resistor pull-up or pull-down for output tristate at power-up. After the eX device is plugged into an electrically active system, the device will not degrade the reliability of or cause damage to the host system. The device's output pins are driven to a high impedance state until normal chip operating conditions are reached. Please see the application note, [Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications](#), which also applies to the eX devices, for more information on hot swapping.

## Power Requirements

Power consumption is extremely low for the eX family due to the low capacitance of the antifuse interconnects. The antifuse architecture does not require active circuitry to hold a charge (as do SRAM or EPROM), making it the lowest-power FPGA architecture available today.

## Low Power Mode

The eX family has been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated when the device enters this mode. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when returning to normal operating mode. I/Os can be driven during LP mode. For details, refer to the [Design for Low Power in Microsemi Antifuse FPGAs](#) application note under the section Using the LP Mode Pin on eX Devices. Clock pins should be driven either HIGH or LOW and should not float; otherwise, they will draw current and burn power. The device must be re-initialized when exiting LP mode.

Table 1-5 describes the different configuration requirements of BST pins and their functionality in different modes.

**Table 1-5 • Boundary-Scan Pin Configurations and Functions**

Mode	Designer "Reserve JTAG" Selection	TAP Controller State
Dedicated (JTAG)	Checked	Any
Flexible (User I/O)	Unchecked	Test-Logic-Reset
Flexible (JTAG)	Unchecked	Any EXCEPT Test-Logic-Reset

## TRST Pin

The TRST pin functions as a dedicated Boundary-Scan Reset pin when the **Reserve JTAG Test Reset** option is selected, as shown in Figure 1-12. An internal pull-up resistor is permanently enabled on the TRST pin in this mode. It is recommended to connect this pin to GND in normal operation to keep the JTAG state controller in the Test-Logic-Reset state. When JTAG is being used, it can be left floating or be driven HIGH.

When the **Reserve JTAG Test Reset** option is not selected, this pin will function as a regular I/O. If unused as an I/O in the design, it will be configured as a tristated output.

## JTAG Instructions

Table 1-6 lists the supported instructions with the corresponding IR codes for eX devices.

**Table 1-6 • JTAG Instruction Code**

Instructions (IR4: IR0)	Binary Code
EXTEST	00000
SAMPLE / PRELOAD	00001
INTTEST	00010
USERCODE	00011
IDCODE	00100
HIGHZ	01110
CLAMP	01111
Diagnostic	10000
BYPASS	11111
Reserved	All others

Table 1-7 lists the codes returned after executing the IDCODE instruction for eX devices. Note that bit 0 is always "1." Bits 11-1 are always "02F", which is Microsemi SoC Products Group's manufacturer code.

**Table 1-7 • IDCODE for eX Devices**

Device	Revision	Bits 31-28	Bits 27-12
eX64	0	8	40B2, 42B2
eX128	0	9	40B0, 42B0
eX256	0	9	40B5, 42B5
eX64	1	A	40B2, 42B2
eX128	1	B	40B0, 42B0
eX256	1	B	40B5, 42B5

## Programming

Device programming is supported through Silicon Sculptor series of programmers. In particular, Silicon Sculptor II is a compact, robust, single-site and multi-site device programmer for the PC.

With standalone software, Silicon Sculptor II allows concurrent programming of multiple units from the same PC, ensuring the fastest programming times possible. Each fuse is subsequently verified by Silicon Sculptor II to insure correct programming. In addition, integrity tests ensure that no extra fuses are programmed. Silicon Sculptor II also provides extensive hardware self-testing capability.

The procedure for programming an eX device using Silicon Sculptor II is as follows:

1. Load the \*.AFM file
2. Select the device to be programmed
3. Begin programming

When the design is ready to go to production, Microsemi offers device volume-programming services either through distribution partners or via in-house programming from the factory.

For more details on programming eX devices, please refer to the [Programming Antifuse Devices](#) application note and the [Silicon Sculptor II User's Guide](#).

## Probing Capabilities

eX devices provide internal probing capability that is accessed with the JTAG pins. The Silicon Explorer II Diagnostic hardware is used to control the TDI, TCK, TMS and TDO pins to select the desired nets for debugging. The user simply assigns the selected internal nets in the Silicon Explorer II software to the PRA/PRB output pins for observation. Probing functionality is activated when the BST pins are in JTAG mode and the TRST pin is driven HIGH or left floating. If the TRST pin is held LOW, the TAP controller will remain in the Test-Logic-Reset state so no probing can be performed. The Silicon Explorer II automatically places the device into JTAG mode, but the user must drive the TRST pin HIGH or allow the internal pull-up resistor to pull TRST HIGH.

When you select the **Reserve Probe Pin** box, as shown in [Figure 1-12 on page 1-10](#), the layout tool reserves the PRA and PRB pins as dedicated outputs for probing. This reserve option is merely a guideline. If the Layout tool requires that the PRA and PRB pins be user I/Os to achieve successful layout, the tool will use these pins for user I/Os. If you assign user I/Os to the PRA and PRB pins and select the **Reserve Probe Pin** option, Designer Layout will override the "Reserve Probe Pin" option and place your user I/Os on those pins.

To allow for probing capabilities, the security fuse must not be programmed. Programming the security fuse will disable the probe circuitry. [Table 1-8 on page 1-13](#) summarizes the possible device configurations for probing once the device leaves the Test-Logic-Reset JTAG state.

## Silicon Explorer II Probe

Silicon Explorer II is an integrated hardware and software solution that, in conjunction with Microsemi Designer software tools, allow users to examine any of the internal nets of the device while it is operating in a prototype or a production system. The user can probe into an eX device via the PRA and PRB pins without changing the placement and routing of the design and without using any additional resources. Silicon Explorer II's noninvasive method does not alter timing or loading effects, thus shortening the debug cycle.

Silicon Explorer II does not require re-layout or additional MUXes to bring signals out to an external pin, which is necessary when using programmable logic devices from other suppliers.

Silicon Explorer II samples data at 100 MHz (asynchronous) or 66 MHz (synchronous). Silicon Explorer II attaches to a PC's standard COM port, turning the PC into a fully functional 18-channel logic analyzer. Silicon Explorer II allows designers to complete the design verification process at their desks and reduces verification time from several hours per cycle to a few seconds.

The Silicon Explorer II tool uses the boundary scan ports (TDI, TCK, TMS and TDO) to select the desired nets for verification. The selected internal nets are assigned to the PRA/PRB pins for observation. [Figure 1-13 on page 1-13](#) illustrates the interconnection between Silicon Explorer II and the eX device to perform in-circuit verification.

Designer software is a place-and-route tool and provides a comprehensive suite of backend support tools for FPGA development. The Designer software includes timing-driven place-and-route, and a world-class integrated static timing analyzer and constraints editor. With the Designer software, a user can lock his/her design pins before layout while minimally impacting the results of place-and-route. Additionally, the back-annotation flow is compatible with all the major simulators and the simulation results can be cross-probed with Silicon Explorer II, Microsemi integrated verification and logic analysis tool. Another tool included in the Designer software is the SmartGen core generator, which easily creates popular and commonly used logic functions for implementation into your schematic or HDL design. Microsemi's Designer software is compatible with the most popular FPGA design entry and verification tools from companies such as Mentor Graphics, Synplicity, Synopsys, and Cadence Design Systems. The Designer software is available for both the Windows and UNIX operating systems.

## Related Documents

### Datasheet

*eX Automotive Family FPGAs*

[www.microsemi.com/soc/documents/eX\\_Auto\\_DS.pdf](http://www.microsemi.com/soc/documents/eX_Auto_DS.pdf)

### Application Notes

*Maximizing Logic Utilization in eX, SX and SX-A FPGA Devices Using CC Macros*

[www.microsemi.com/soc/documents/CC\\_Macro\\_AN.pdf](http://www.microsemi.com/soc/documents/CC_Macro_AN.pdf)

*Implementation of Security in Microsemi Antifuse FPGAs*

[www.microsemi.com/soc/documents/Antifuse\\_Security\\_AN.pdf](http://www.microsemi.com/soc/documents/Antifuse_Security_AN.pdf)

*Microsemi eX, SX-A, and RT54SX-S I/Os*

[www.microsemi.com/soc/documents/antifuseIO\\_AN.pdf](http://www.microsemi.com/soc/documents/antifuseIO_AN.pdf)

*Microsemi SX-A and RT54SX-S Devices in Hot-Swap and Cold-Sparing Applications*

[www.microsemi.com/soc/documents/HotSwapColdSparing\\_AN.pdf](http://www.microsemi.com/soc/documents/HotSwapColdSparing_AN.pdf)

*Design For Low Power in Microsemi Antifuse FPGAs*

[www.microsemi.com/soc/documents/Low\\_Power\\_AN.pdf](http://www.microsemi.com/soc/documents/Low_Power_AN.pdf)

*Programming Antifuse Devices*

[www.microsemi.com/soc/documents/AntifuseProgram\\_AN.pdf](http://www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf)

### User Guides

*Silicon Sculptor II User's Guide*

[www.microsemi.com/soc/documents/SiliSculptII\\_Sculpt3\\_ug.pdf](http://www.microsemi.com/soc/documents/SiliSculptII_Sculpt3_ug.pdf)

### Miscellaneous

*Libero IDE flow*

[www.microsemi.com/soc/products/tools/libero/flow.html](http://www.microsemi.com/soc/products/tools/libero/flow.html)

## 2.5 V / 3.3 V /5.0 V Operating Conditions

**Table 1-9 • Absolute Maximum Ratings\***

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	−0.3 to +6.0	V
VCCA	DC Supply Voltage for Array	−0.3 to +3.0	V
VI	Input Voltage	−0.5 to +5.75	V
VO	Output Voltage	−0.5 to +V <sub>CCI</sub>	V
T <sub>STG</sub>	Storage Temperature	−65 to +150	°C

**Note:** \*Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the Recommended Operating Conditions.

**Table 1-10 • Recommended Operating Conditions**

Parameter	Commercial	Industrial	Units
Temperature Range*	0 to +70	−40 to +85	°C
2.5V Power Supply Range (VCCA, VCCI)	2.3 to 2.7	2.3 to 2.7	V
3.3V Power Supply Range (VCCI)	3.0 to 3.6	3.0 to 3.6	V
5.0V Power Supply Range (VCCI)	4.75 to 5.25	4.75 to 5.25	V

**Note:** \*Ambient temperature ( $T_A$ ).

**Table 1-11 • Typical eX Standby Current at 25°C**

Product	VCCA = 2.5 V VCCI = 2.5 V	VCCA = 2.5 V VCCI = 3.3 V	VCCA = 2.5 V VCCI = 5.0 V
eX64	397 $\mu$ A	497 $\mu$ A	700 $\mu$ A
eX128	696 $\mu$ A	795 $\mu$ A	1,000 $\mu$ A
eX256	698 $\mu$ A	796 $\mu$ A	2,000 $\mu$ A



## Power Dissipation

Power consumption for eX devices can be divided into two components: static and dynamic.

### Static Power Component

The power due to standby current is typically a small component of the overall power. Typical standby current for eX devices is listed in the [Table 1-11 on page 1-16](#). For example, the typical static power for eX128 at 3.3 V  $V_{CCI}$  is:

$$I_{CC} * V_{CCA} = 795 \mu A * 2.5 V = 1.99 mW$$

### Dynamic Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. This component is frequency-dependent and a function of the logic and the external I/O. Dynamic power dissipation results from charging internal chip capacitance due to PC board traces and load device inputs. An additional component of the dynamic power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent dynamic power dissipation.

$$\text{Dynamic power dissipation} = C_{EQ} * V_{CCA}^2 * F$$

where:

$C_{EQ}$  = Equivalent capacitance

$F$  = switching frequency

Equivalent capacitance is calculated by measuring  $I_{CCA}$  at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

### CEQ Values for eX Devices

Combinatorial modules ( $C_{eqcm}$ )	1.70 pF
Sequential modules ( $C_{eqsm}$ )	1.70 pF
Input buffers ( $C_{eqi}$ )	1.30 pF
Output buffers ( $C_{eqo}$ )	7.40 pF
Routed array clocks ( $C_{eqcr}$ )	1.05 pF

The variable and fixed capacitance of other device components must also be taken into account when estimating the dynamic power dissipation.

[Table 1-12](#) shows the capacitance of the clock components of eX devices.

**Table 1-12 • Capacitance of Clock Components of eX Devices**

	eX64	eX128	eX256
Dedicated array clock – variable ( $C_{eqhv}$ )	0.85 pF	0.85 pF	0.85 pF
Dedicated array clock – fixed ( $C_{eqhf}$ )	18.00 pF	20.00 pF	25.00 pF
Routed array clock A (r1)	23.00 pF	28.00 pF	35.00 pF
Routed array clock B (r2)	23.00 pF	28.00 pF	35.00 pF

## Thermal Characteristics

The temperature variable in the Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because the heat generated from dynamic power consumption is usually hotter than the ambient temperature. EQ 1, shown below, can be used to calculate junction temperature.

EQ 1

$$\text{Junction Temperature} = \Delta T + T_a(1)$$

Where:

$T_a$  = Ambient Temperature

$\Delta T$  = Temperature gradient between junction (silicon) and ambient =  $\theta_{ja} * P$

P = Power

$\theta_{ja}$  = Junction to ambient of package.  $\theta_{ja}$  numbers are located in the "Package Thermal Characteristics" section below.

## Package Thermal Characteristics

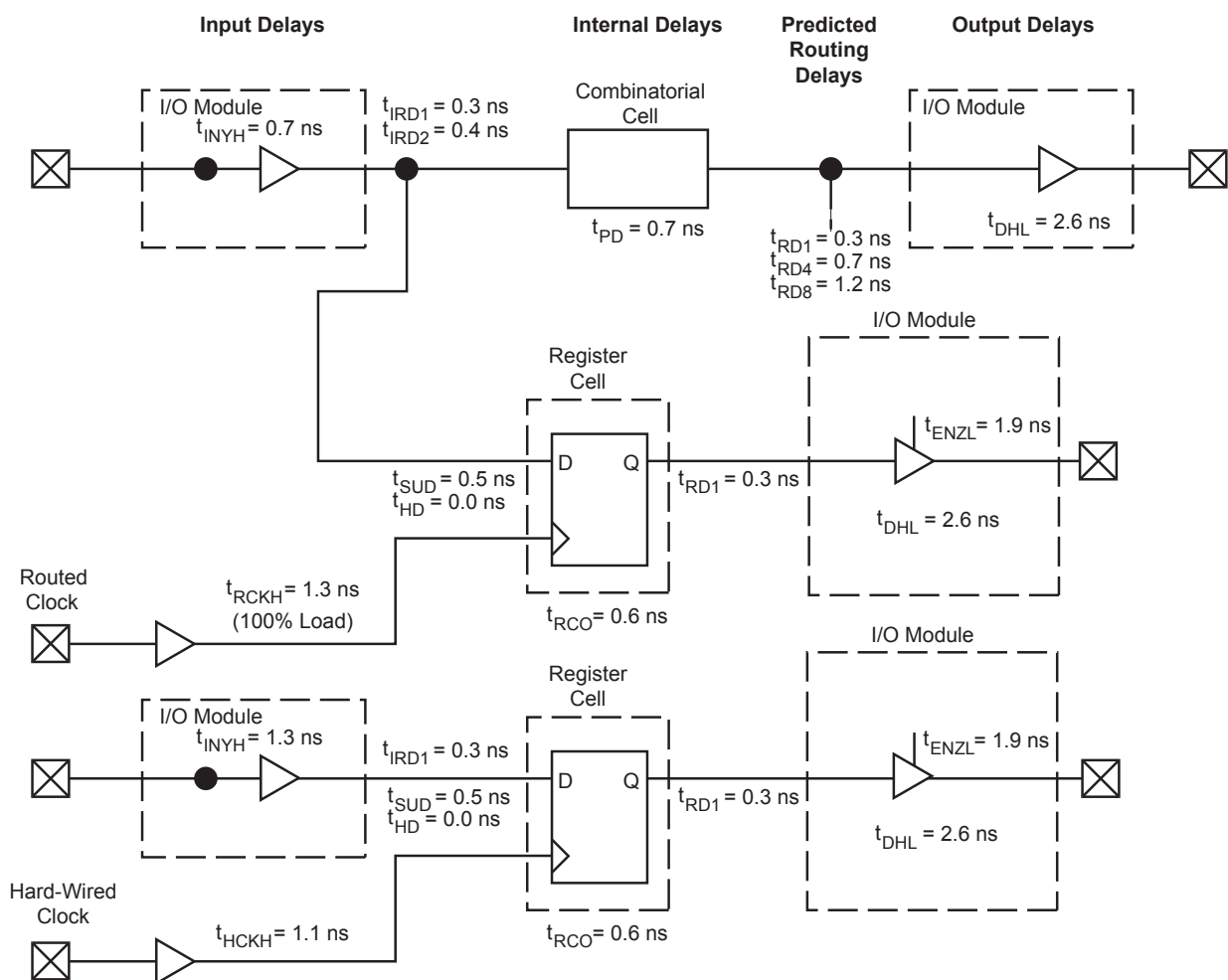
The device junction-to-case thermal characteristic is  $\theta_{jc}$ , and the junction-to-ambient air characteristic is  $\theta_{ja}$ . The thermal characteristics for  $\theta_{ja}$  are shown with two different air flow rates.  $\theta_{jc}$  is provided for reference. The maximum junction temperature is 150°C.

The maximum power dissipation allowed for eX devices is a function of  $\theta_{ja}$ . A sample calculation of the absolute maximum power dissipation allowed for a TQFP 100-pin package at commercial temperature and still air is as follows:

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (}^\circ\text{C)} - \text{Max. ambient temp. (}^\circ\text{C)}}{\theta_{ja} (^\circ\text{C/W)}} = \frac{150^\circ\text{C} - 70^\circ\text{C}}{33.5^\circ\text{C/W}} = 2.39\text{W}$$

Package Type	Pin Count	$\theta_{jc}$	$\theta_{ja}$			Units
			Still Air	1.0 m/s 200 ft/min	2.5 m/s 500 ft/min	
Thin Quad Flat Pack (TQFP)	64	12.0	42.4	36.3	34.0	°C/W
Thin Quad Flat Pack (TQFP)	100	14.0	33.5	27.4	25.0	°C/W

## eX Timing Model



*Note:* Values shown for eX128-P, worst-case commercial conditions (5.0 V, 35 pF Pad Load).

**Figure 1-14 • eX Timing Model**

### Hardwired Clock

$$\text{External Setup} = t_{INYH} + t_{IRD1} + t_{SUD} - t_{HCKH}$$

$$= 0.7 + 0.3 + 0.5 - 1.1 = 0.4 \text{ ns}$$

Clock-to-Out (Pad-to-Pad), typical

$$= t_{HCKH} + t_{RCO} + t_{RD1} + t_{DHL}$$

$$= 1.1 + 0.6 + 0.3 + 2.6 = 4.6 \text{ ns}$$

### Routed Clock

$$\text{External Setup} = t_{INYH} + t_{IRD2} + t_{SUD} - t_{RCKH}$$

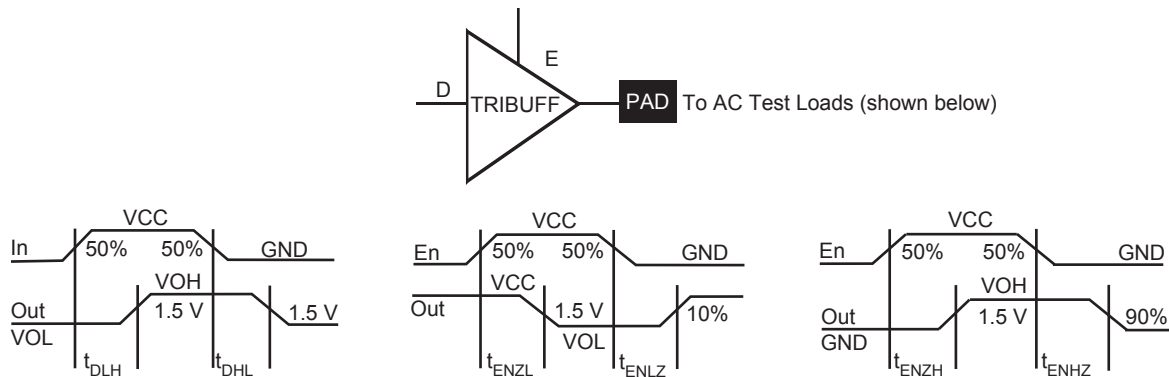
$$= 0.7 + 0.4 + 0.5 - 1.3 = 0.3 \text{ ns}$$

Clock-to-Out (Pad-to-Pad), typical

$$= t_{RCKH} + t_{RCO} + t_{RD1} + t_{DHL}$$

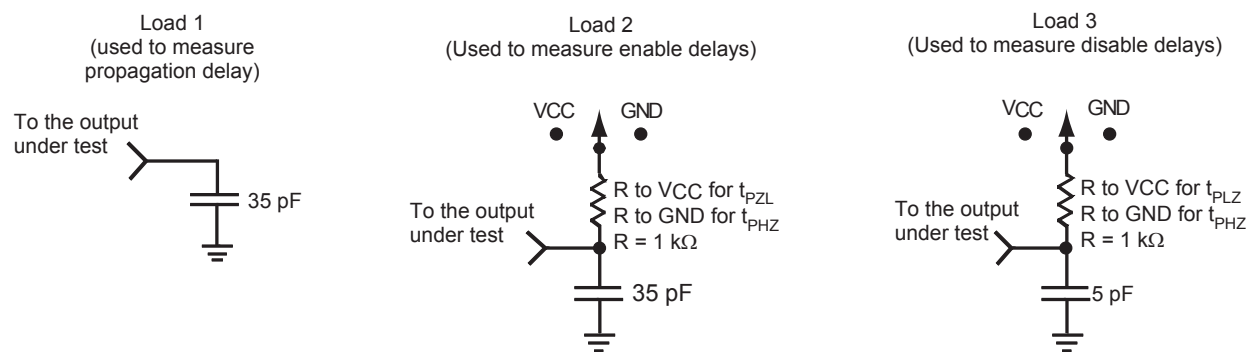
$$= 1.3 + 0.6 + 0.3 + 2.6 = 4.8 \text{ ns}$$

## Output Buffer Delays



**Table 1-13 • Output Buffer Delays**

## AC Test Loads



**Figure 1-15 • AC Test Loads**

## Timing Characteristics

Timing characteristics for eX devices fall into three categories: family-dependent, device-dependent, and design-dependent. The input and output buffer characteristics are common to all eX family members. Internal routing delays are device-dependent. Design dependency means actual delays are not determined until after placement and routing of the user's design are complete. Delay values may then be determined by using the Timer utility or performing simulation with post-layout delays.

### Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing critical paths. Critical nets are determined by net property assignment prior to placement and routing. Up to six percent of the nets in a design may be designated as critical.

### Long Tracks

Some nets in the design use long tracks. Long tracks are special routing resources that span multiple rows, columns, or modules. Long tracks employ three to five antifuse connections. This increases capacitance and resistance, resulting in longer net delays for macros connected to long tracks. Typically, no more than six percent of nets in a fully utilized device require long tracks. Long tracks contribute approximately 4 ns to 8.4 ns delay. This additional delay is represented statistically in higher fanout routing delays.

### Timing Derating

eX devices are manufactured with a CMOS process. Therefore, device performance varies according to temperature, voltage, and process changes. Minimum timing parameters reflect maximum operating voltage, minimum operating temperature, and best-case processing. Maximum timing parameters reflect minimum operating voltage, maximum operating temperature, and worst-case processing.

### Temperature and Voltage Derating Factors

**Table 1-16 • Temperature and Voltage Derating Factors**  
(Normalized to Worst-Case Commercial,  $T_J = 70^\circ\text{C}$ ,  $V_{CCA} = 2.3\text{V}$ )

VCCA	Junction Temperature ( $T_J$ )						
	–55	–40	0	25	70	85	125
2.3	0.79	0.80	0.87	0.88	1.00	1.04	1.13
2.5	0.74	0.74	0.81	0.83	0.93	0.97	1.06
2.7	0.69	0.70	0.76	0.78	0.88	0.91	1.00

**TMS                      Test Mode Select**

The TMS pin controls the use of the IEEE 1149.1 Boundary scan pins (TCK, TDI, TDO, TRST). In flexible mode when the TMS pin is set LOW, the TCK, TDI, and TDO pins are boundary scan pins (refer to [Table 1-4 on page 1-10](#)). Once the boundary scan pins are in test mode, they will remain in that mode until the internal boundary scan state machine reaches the “logic reset” state. At this point, the boundary scan pins will be released and will function as regular I/O pins. The “logic reset” state is reached five TCK cycles after the TMS pin is set HIGH. In dedicated test mode, TMS functions as specified in the IEEE 1149.1 specifications.

**TRST, I/O                      Boundary Scan Reset Pin**

Once it is configured as the JTAG Reset pin, the TRST pin functions as an active-low input to asynchronously initialize or reset the boundary scan circuit. The TRST pin is equipped with an internal pull-up resistor. This pin functions as an I/O when the **Reserve JTAG Reset** Pin is not selected in the Designer software.

**VCCI                      Supply Voltage**

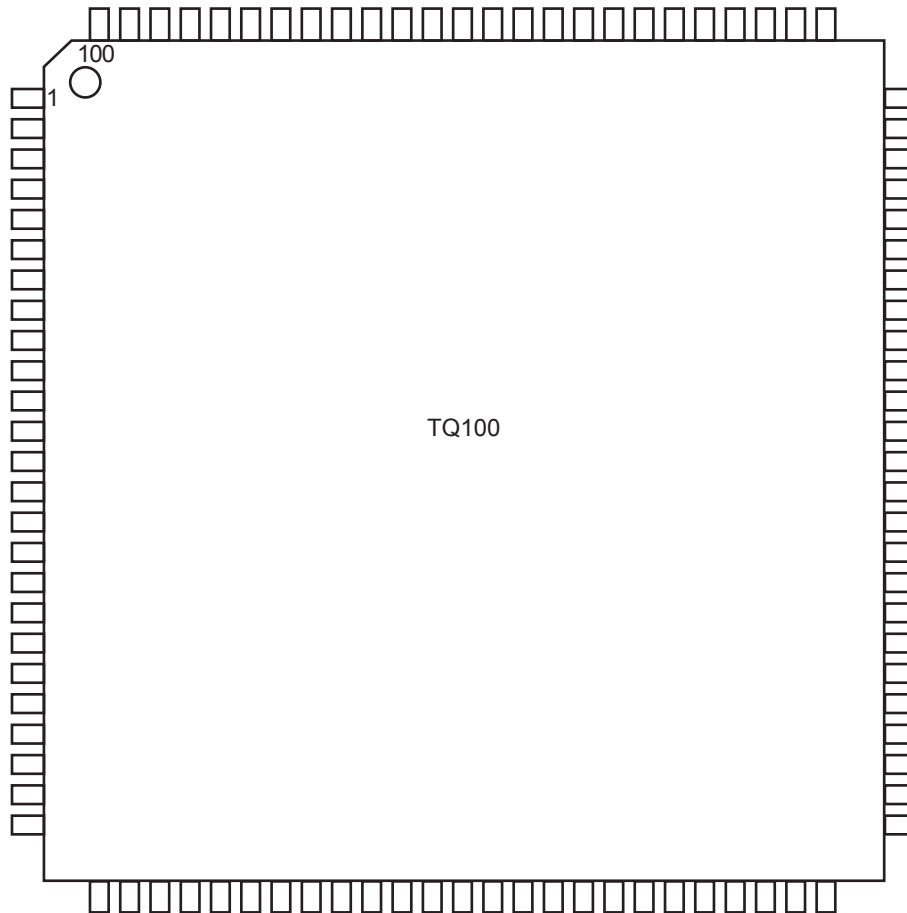
Supply voltage for I/Os.

**VCCA                      Supply Voltage**

Supply voltage for Array.

## TQ100

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**Note:** For Package Manufacturing and Environmental information, visit Resource center at [www.microsemi.com/soc/products/rescenter/package/index.html](http://www.microsemi.com/soc/products/rescenter/package/index.html).

TQ100			
Pin Number	eX64 Function	eX128 Function	eX256 Function
71	I/O	I/O	I/O
72	NC	I/O	I/O
73	NC	NC	I/O
74	NC	NC	I/O
75	NC	NC	I/O
76	NC	I/O	I/O
77	I/O	I/O	I/O
78	I/O	I/O	I/O
79	I/O	I/O	I/O
80	I/O	I/O	I/O
81	I/O	I/O	I/O
82	VCCI	VCCI	VCCI
83	I/O	I/O	I/O
84	I/O	I/O	I/O
85	I/O	I/O	I/O
86	I/O	I/O	I/O
87	CLKA	CLKA	CLKA
88	CLKB	CLKB	CLKB
89	NC	NC	NC
90	VCCA	VCCA	VCCA
91	GND	GND	GND
92	PRA, I/O	PRA, I/O	PRA, I/O
93	I/O	I/O	I/O
94	I/O	I/O	I/O
95	I/O	I/O	I/O
96	I/O	I/O	I/O
97	I/O	I/O	I/O
98	I/O	I/O	I/O
99	I/O	I/O	I/O
100	TCK, I/O	TCK, I/O	TCK, I/O

**Note:** \*Please read the LP pin descriptions for restrictions on their use.





## 3 – Datasheet Information

### List of Changes

The following table lists critical changes that were made in the current version of the document.

Revision	Changes	Page
Revision 10 (October 2012)	The "User Security" section was revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement industry standard security (SAR 34677).	1-5
	Package names used in the "Product Profile" section and "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 34779).	I 2-1
Revision 9 (June 2011)	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "eX Device Status" table indicates the status for each device in the device family.	II
	The Chip Scale packages (CS49, CS128, CS181) are no longer offered for eX devices. They have been removed from the product family information. Pin tables for CSP packages have been removed from the datasheet (SAR 32002).	N/A
Revision 8 (v4.3, June 2006)	The "Ordering Information" was updated with RoHS information. The TQFP measurement was also updated.	II
	The "Dedicated Test Mode" was updated.	1-10
	Note 5 was added to the "3.3 V LVTTTL Electrical Specifications" and "5.0 V TTL Electrical Specifications" tables	1-18
	The "LP Low Power Pin" description was updated.	1-31
Revision 7 (v4.2, June 2004)	The "eX Timing Model" was updated.	1-22
v4.1	The "Development Tool Support" section was updated.	1-13
	The "Package Thermal Characteristics" section was updated.	1-21
v4.0	The "Product Profile" section was updated.	1-I
	The "Ordering Information" section was updated.	1-II
	The "Temperature Grade Offerings" section is new.	1-III
	The "Speed Grade and Temperature Grade Matrix" section is new.	1-III
	The "eX FPGA Architecture and Characteristics" section was updated.	1-1
	The "Clock Resources" section was updated.	1-3
	Table 1-1 •Connections of Routed Clock Networks, CLKA and CLKB is new.	1-4
	The "User Security" section was updated.	1-5
	The "I/O Modules" section was updated.	1-5
	The "Hot-Swapping" section was updated.	1-6
	The "Power Requirements" section was updated.	1-6
	The "Low Power Mode" section was updated.	1-6
	The "Boundary Scan Testing (BST)" section was updated.	1-10
	The "Dedicated Test Mode" section was updated.	1-10

## Datasheet Categories

### **Categories**

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the ["eX Device Status" table on page II](#), is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

#### **Product Brief**

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

#### **Advance**

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

#### **Preliminary**

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

#### **Production**

This version contains information that is considered to be final.

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